

L Number	Hits	Search Text	DB	Time stamp
-	207	(mfs MFMIS) with (ferroelectric ferro-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 12:44
-	109	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:59
-	12	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:58
-	14498	(mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:06
-	3093	((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:08
-	29	((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 12:55
-	18496	(mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:07
-	3302	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:09
-	29	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	10	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55
-	10	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and (ferroelectric adj3 capacitor) and (gate adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55
-	4	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds voltage)) and ((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00

-	205	((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	40	((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFMIS))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	32	((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFMIS)) and (writ\$3 program\$4) and (read\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
-	16	(((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFMIS)) and (writ\$3 program\$4) and (read\$3)) and ((ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
-	5690	read\$3 same ((voltage potential bias) with drain with source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:17
-	574	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:17
-	22	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (nonvolatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:19
-	2835	(read\$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:20
-	5	((((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (nonvolatile non-volatile)) and ((read\$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:23
-	124614	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:25
-	22	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and ((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:25
-	1	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and ((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile)) and ((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:27
-	1	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and ((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:27

-	224	(read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:30
-	181	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:16
-	1	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:29
-	1669	read\$3 same ((appl\$3 near3 (voltage bias potential)) with source with drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:33
-	3	((unsaturat\$3 non-saturat\$3) near3 region) and (saturat\$3 near3 region)) and (read\$3 same ((appl\$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:45
-	11	((unsaturat\$3 non-saturat\$3) near3 region) with read\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	1	((unsaturat\$3 non-saturat\$3) near3 region) with read\$3) and (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:52
-	3769	(unsaturat\$3 non-saturat\$3) with read\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	3779	(unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	200	((unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3) and (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:54
-	200	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3) and (non-volatile nonvolatile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:04
-	28	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3) and (non-volatile nonvolatile))) and (read reading)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:09
-	8	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((unsaturat\$3 non-saturat\$3 nonsaturat\$3) with read\$3) and (non-volatile nonvolatile))) and (read reading)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:09

-	1	((read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source with drain)) and ((unsaturat\$3 non-saturat\$3 nonsaturat\$3) near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:19
-	1	read\$3 with (unsaturat\$3 non-saturat\$3 nonsaturat\$3) with (current near3 detect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:20